

# DATA SHEET

**BUJ103AX**

**Silicon Diffused Power Transistor**

Product specification

August 2018

## Silicon Diffused Power Transistor

## BUJ103AX

## GENERAL DESCRIPTION

High-voltage, high-speed planar-passivated npn power switching transistor in a plastic full-pack envelope intended for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

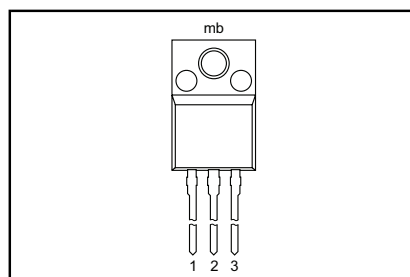
## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	700	V
$V_{CBO}$	Collector-Base voltage (open emitter)		-	700	V
$V_{CEO}$	Collector-emitter voltage (open base)		-	400	V
$I_C$	Collector current (DC)		-	4	A
$I_{CM}$	Collector current peak value		-	8	A
$P_{tot}$	Total power dissipation	$T_{hs} \leq 25\text{ °C}$	-	26	W
$V_{CESat}$	Collector-emitter saturation voltage		0.25	1.0	V
$h_{FEsat}$	DC current gain	$I_C = 3\text{ A}; V_{CE} = 5\text{ V}$	12.5	-	
$t_f$	Fall time	$I_C = 2\text{ A}, I_{B1} = 0.4\text{ A}$	33	80	ns

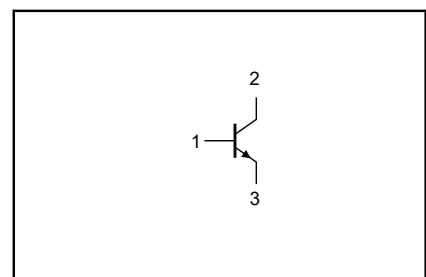
## PINNING - SOT186A

PIN	DESCRIPTION
1	base
2	collector
3	emitter
mb	solated

## PIN CONFIGURATION



## SYMBOL



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CESM}$	Collector to emitter voltage	$V_{BE} = 0\text{ V}$	-	700	V
$V_{CEO}$	Collector to emitter voltage (open base)		-	400	V
$V_{CBO}$	Collector to base voltage (open emitter)		-	700	V
$I_C$	Collector current (DC)		-	4	A
$I_{CM}$	Collector current peak value		-	8	A
$I_B$	Base current (DC)		-	2	A
$I_{BM}$	Base current peak value		-	4	A
$P_{tot}$	Total power dissipation	$T_{hs} \leq 25\text{ °C}$	-	26	W
$T_{stg}$	Storage temperature		-65	150	°C
$T_j$	Junction temperature		-	150	°C

## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-hs}$	Junction to heatsink	with heatsink compound	-	4.8	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	55	-	K/W

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**ISOLATION LIMITING VALUE & CHARACTERISTIC** $T_{hs} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{isol}$	R.M.S. isolation voltage from all three terminals to external heatsink	$f = 50\text{-}60\text{ Hz}$ ; sinusoidal waveform; $R.H. \leq 65\%$ ; clean and dustfree	-		2500	V
$C_{isol}$	Capacitance from T2 to external heatsink	$f = 1\text{ MHz}$	-	10	-	pF

**STATIC CHARACTERISTICS** $T_{hs} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CES}$	Collector cut-off current <sup>1</sup>	$V_{BE} = 0\text{ V}$ ; $V_{CE} = V_{CESMmax}$ $V_{BE} = 0\text{ V}$ ; $V_{CE} = V_{CESMmax}$ $T_j = 125\text{ }^{\circ}\text{C}$	-	-	1.0	mA
$I_{CBO}$	Collector cut-off current <sup>1</sup>	$V_{CBO} = V_{CESMmax}(700\text{V})$ $V_{CEO} = V_{CEOMmax}(400\text{V})$	-	-	0.1	mA
$I_{CEO}$	Collector cut-off current <sup>1</sup>	$V_{CBO} = V_{CESMmax}(700\text{V})$ $V_{CEO} = V_{CEOMmax}(400\text{V})$	-	-	0.1	mA
$I_{EBO}$	Emitter cut-off current	$V_{EB} = 7\text{ V}$ ; $I_C = 0\text{ A}$	-	-	0.1	mA
$V_{CEOsust}$	Collector-emitter sustaining voltage	$I_B = 0\text{ A}$ ; $I_C = 10\text{ mA}$ ; $L = 25\text{ mH}$	400	-	-	V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C = 3.0\text{ A}$ ; $I_B = 0.6\text{ A}$	-	0.25	1.0	V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C = 3.0\text{ A}$ ; $I_B = 0.6\text{ A}$	-	0.97	1.5	V
$h_{FE}$	DC current gain	$I_C = 1\text{ mA}$ ; $V_{CE} = 5\text{ V}$	10	17	32	
$h_{FE}$	DC current gain	$I_C = 0.5\text{ A}$ ; $V_{CE} = 5\text{ V}$	12	20	32	
$h_{FEsat}$	DC current gain	$I_C = 2\text{ A}$ ; $V_{CE} = 5\text{ V}$	13.5	16	20	
$h_{FEsat}$	DC current gain	$I_C = 3\text{ A}$ ; $V_{CE} = 5\text{ V}$	-	12.5	-	

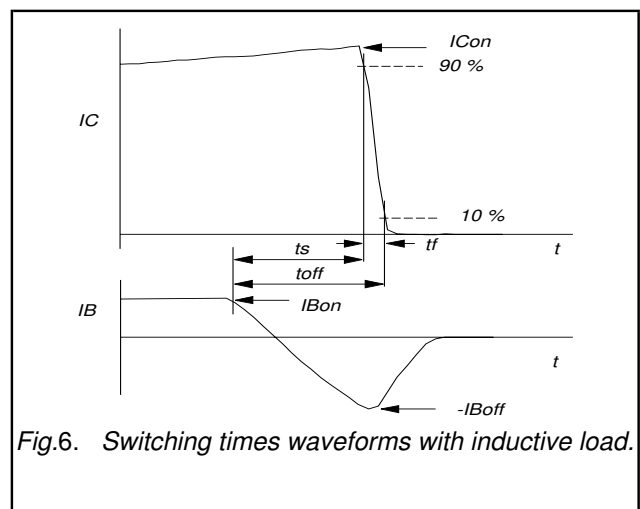
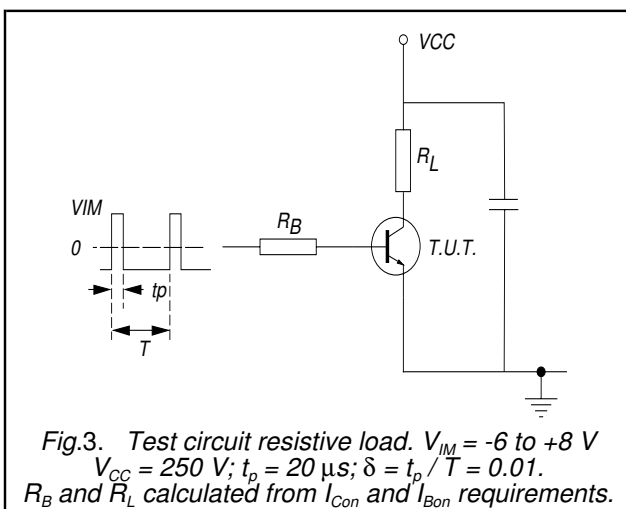
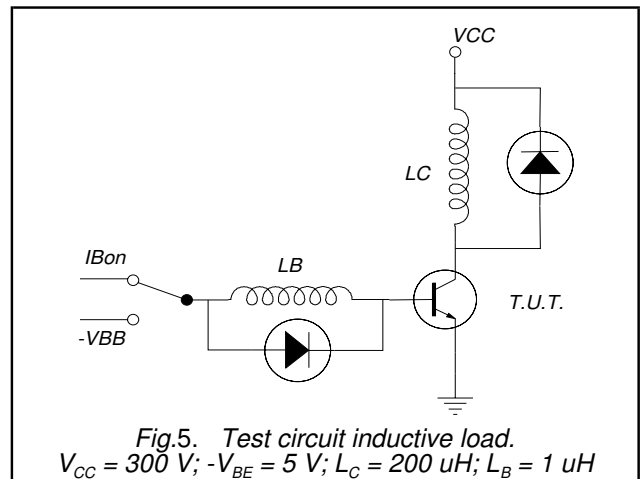
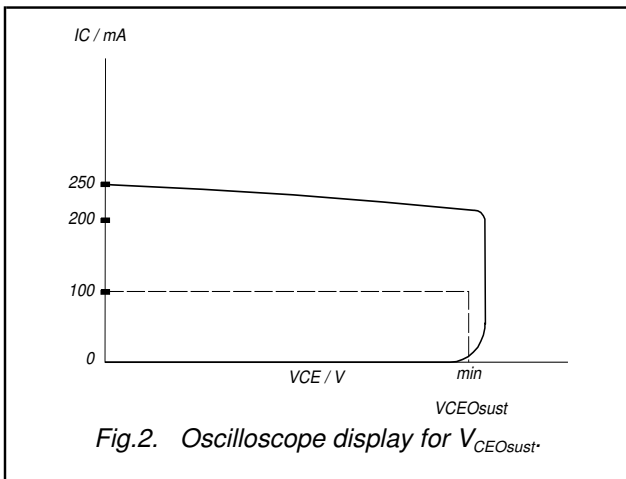
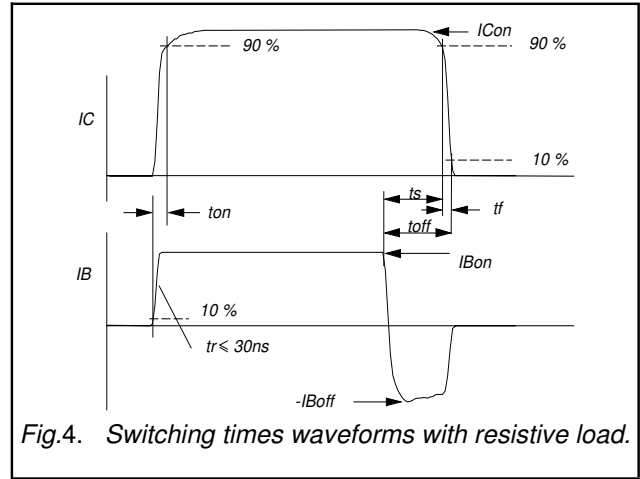
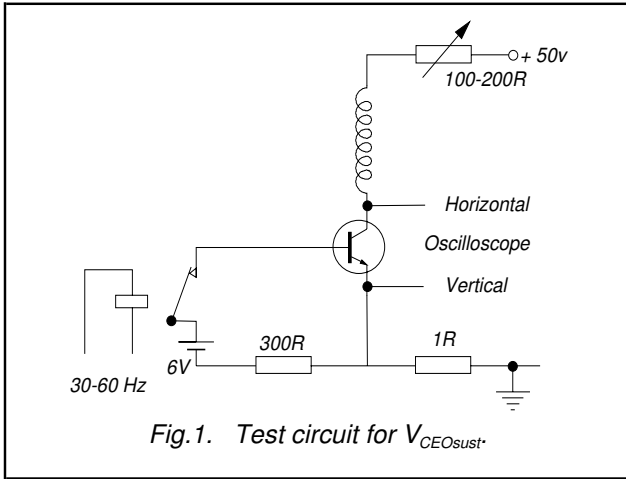
**DYNAMIC CHARACTERISTICS** $T_{hs} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
	Switching times (resistive load)	$I_{Con} = 2.5\text{ A}$ ; $I_{Bon} = -I_{Boff} = 0.5\text{ A}$ ; $R_L = 75\text{ ohms}$ ; $V_{BB2} = 4\text{ V}$ ;			
$t_{on}$	Turn-on time		0.52	0.6	$\mu\text{s}$
$t_s$	Turn-off storage time		2.7	3.2	$\mu\text{s}$
$t_f$	Turn-off fall time		0.3	0.43	$\mu\text{s}$
	Switching times (inductive load)	$I_{Con} = 2\text{ A}$ ; $I_{Bon} = 0.4\text{ A}$ ; $L_B = 1\text{ }\mu\text{H}$ ; $-V_{BB} = 5\text{ V}$			
$t_s$	Turn-off storage time		1.2	1.33	$\mu\text{s}$
$t_f$	Turn-off fall time		33	80	ns
	Switching times (inductive load)	$I_{Con} = 2\text{ A}$ ; $I_{Bon} = 0.4\text{ A}$ ; $L_B = 1\text{ }\mu\text{H}$ ; $-V_{BB} = 5\text{ V}$ ; $T_j = 100\text{ }^{\circ}\text{C}$			
$t_s$	Turn-off storage time		-	1.8	$\mu\text{s}$
$t_f$	Turn-off fall time		-	200	ns

1 Measured with half sine-wave voltage (curve tracer).

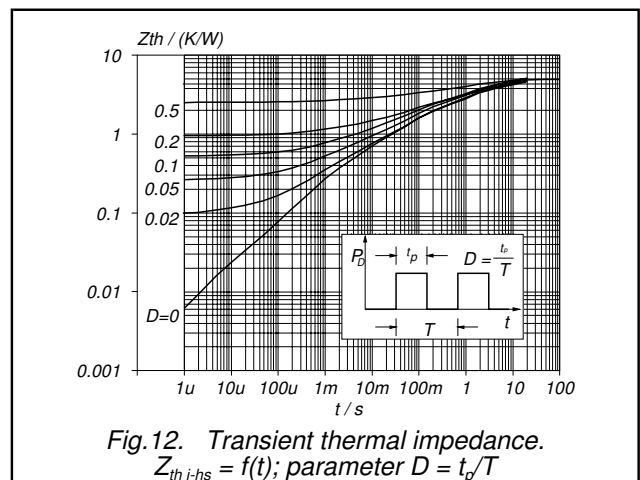
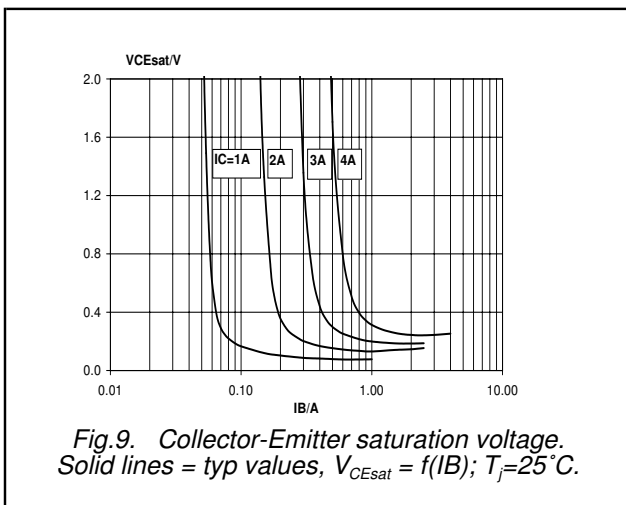
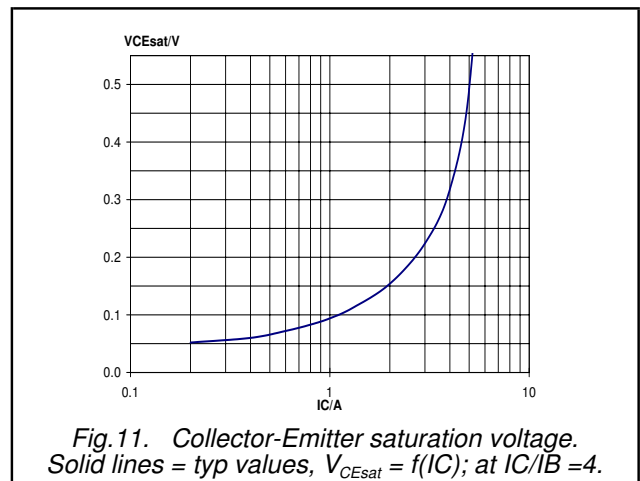
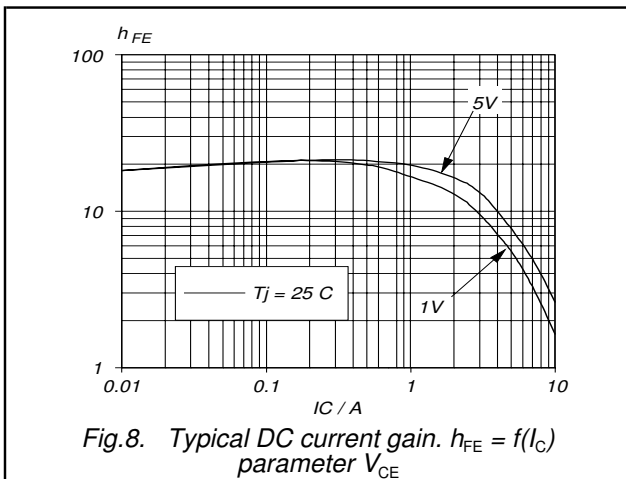
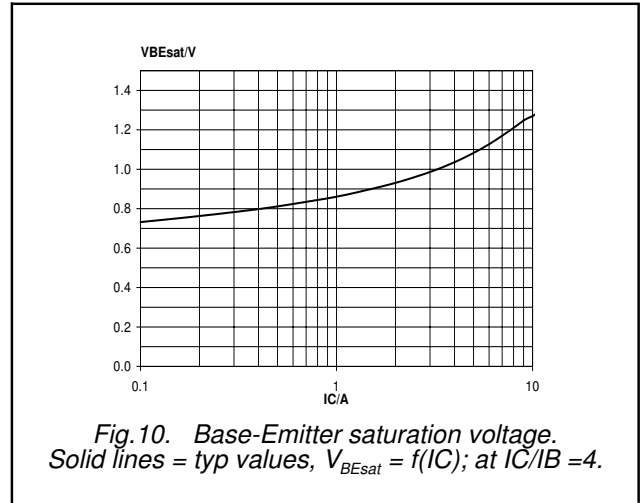
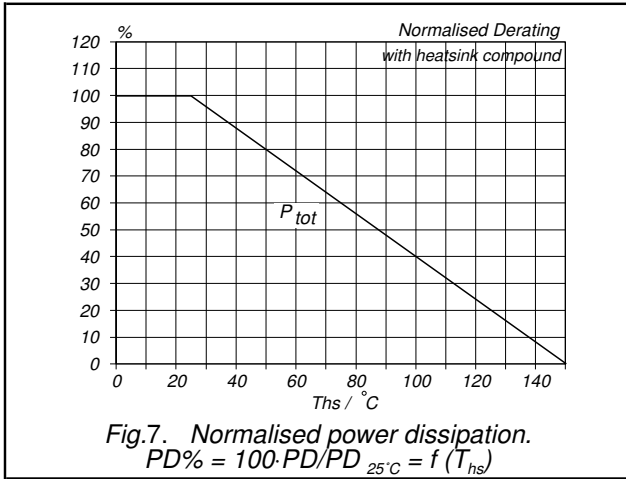
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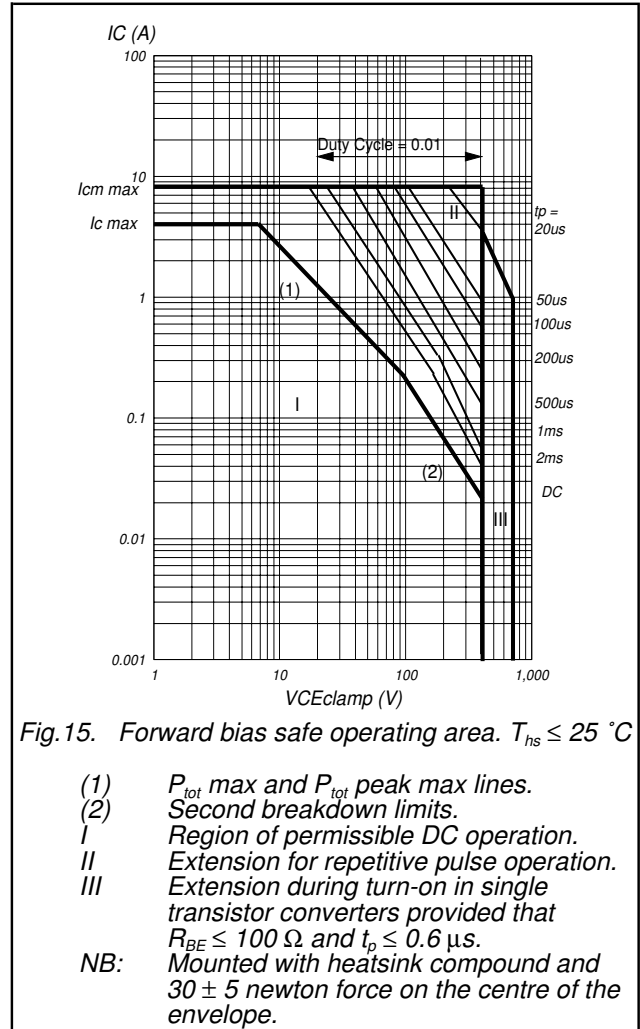
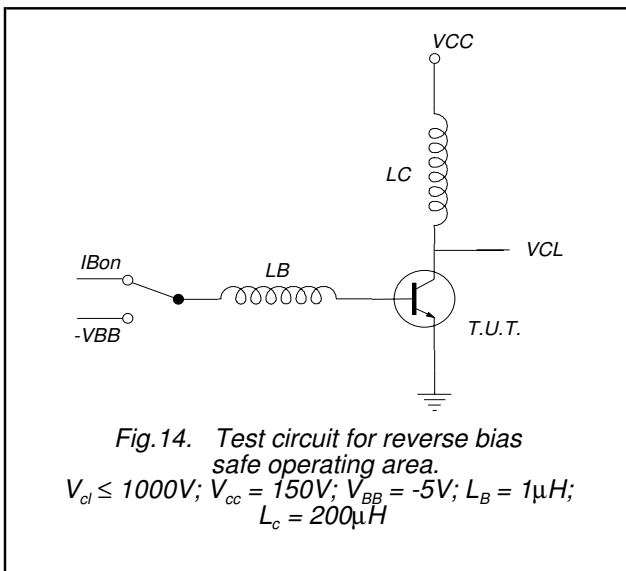
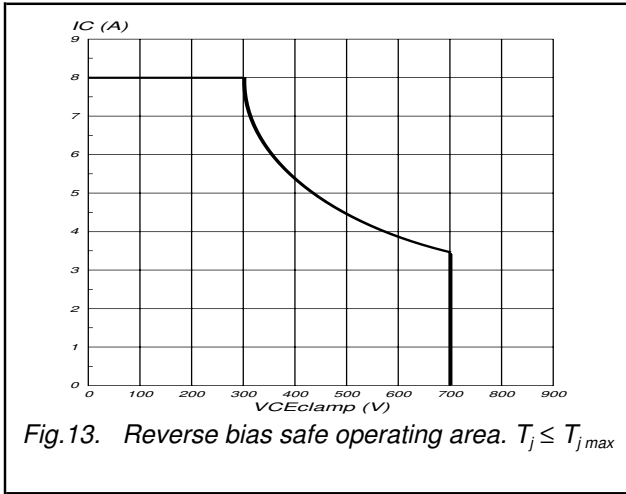
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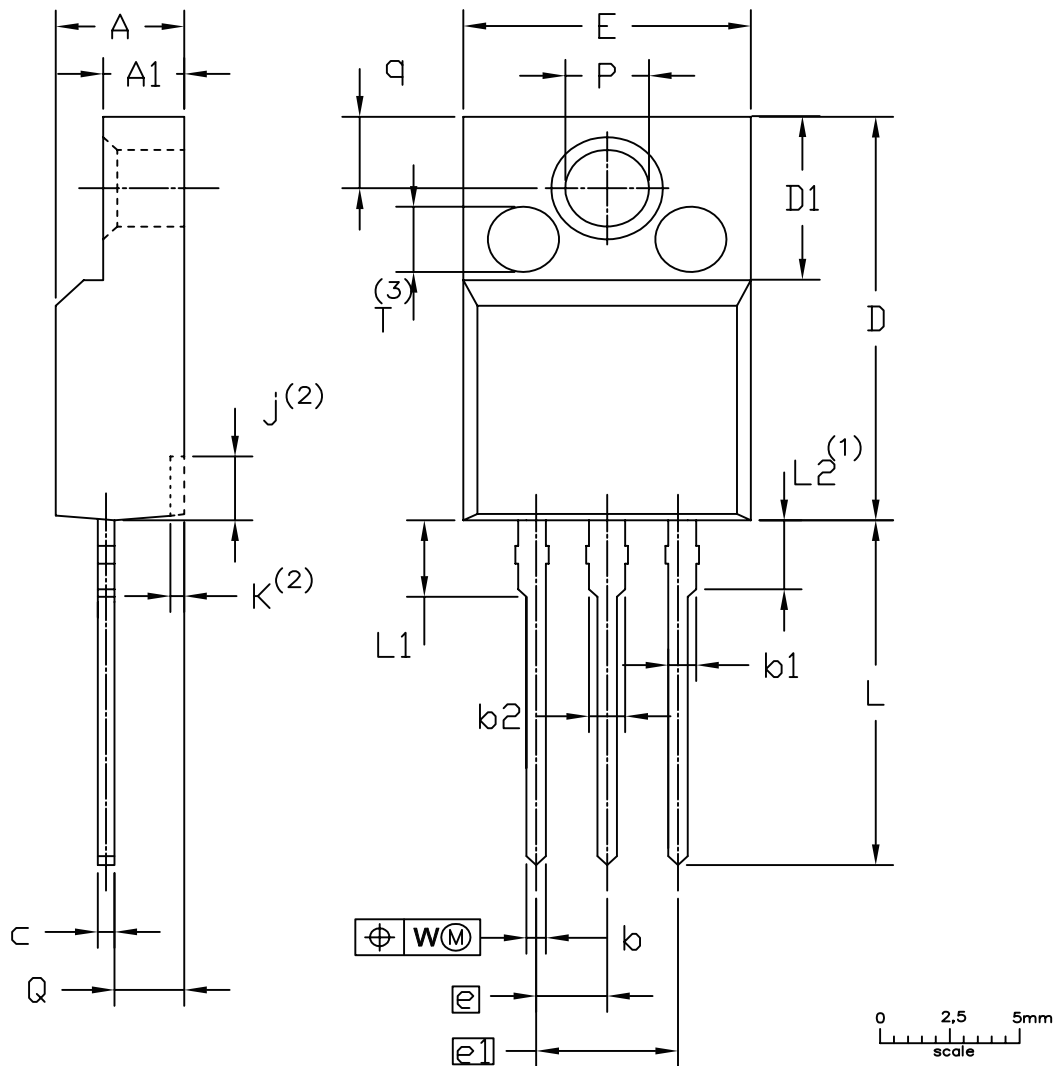
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MECHANICAL DATA

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"

SOT186A



UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	c	D	D <sub>1</sub>	E	e	e <sub>1</sub>	j <sup>(2)</sup>	k <sup>(2)</sup>	L	L <sub>1</sub>	L <sub>2</sub> <sup>(1)</sup> max.	P	Q	q	W	T <sup>(3)</sup>
mm	4.6	2.9	0.9	1.1	1.4	0.7	15.8	6.5	10.3			2.7	0.6	14.4	3.30		3.2	2.6	3.0	0.4	2.5
	4.0	2.5	0.7	0.9	1.0	0.4	15.2	6.3	9.7	2.54	5.08	1.7	0.4	13.5	2.79	3	3.0	2.3	2.6		

Notes

1. Terminal dimensions within this zone are uncontrolled
2. Dot lines area designs may vary
3. Eject pin mark is for reference only

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT186A		3 LEADS TO220F			2013-11-14

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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